

# **PHPT61006PY**

## 100 V, 6 A PNP high power bipolar transistor

21 January 2015

**Product data sheet** 

## 1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT61006NY

#### 2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

## 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- · Relay replacement

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-100	V
I <sub>C</sub>	collector current		-	-	-6	Α
I <sub>CM</sub>	peak collector current	t <sub>p</sub> ≤ 1 ms; single pulse	-	-	-12	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -6 A; $I_B$ = -600 mA; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_{amb}$ = 25 °C; pulsed	-	85	270	mΩ



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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	Е	emitter		В—
3	Е	emitter	[d	'*_
4	В	base	<u>o o o o</u>	sym132
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

## 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PHPT61006PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT61006PY	1006PAB

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## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-100	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-100	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-8	V
I <sub>C</sub>	collector current			-	-6	Α
I <sub>CM</sub>	peak collector current	t <sub>p</sub> ≤ 1 ms; single pulse		-	-12	Α
I <sub>B</sub>	base current			-	-1	Α
I <sub>BM</sub>	peak base current	t <sub>p</sub> ≤ 1 ms; pulsed		-	-2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.3	W
			[2]	-	3.3	W
			[3]	-	5	W
			[4]	-	25	W
T <sub>j</sub>	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

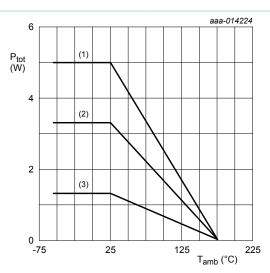
<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board ( PCB), single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

<sup>[3]</sup> Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

<sup>[4]</sup> Power dissipation from junction to mounting base.

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- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient			[1]	-	-	115	K/W
		<u>[2]</u>	-	-	45	K/W	
ambient		[3]	-	-	30	K/W	
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

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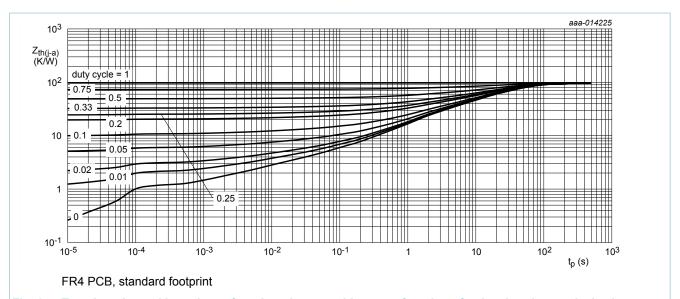


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

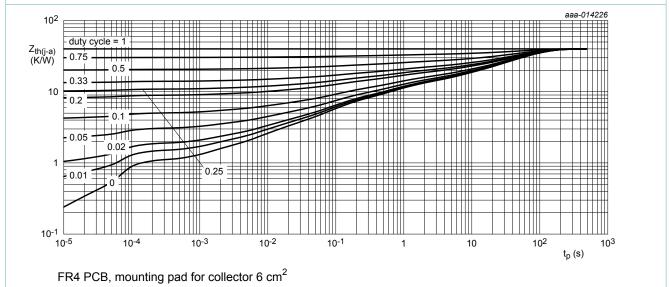


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

Table 7. Characteristics

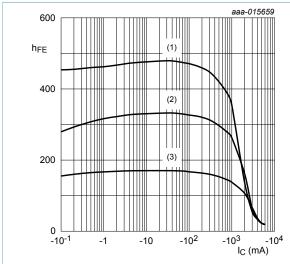
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = -80 V; $I_E$ = 0 A; $T_{amb}$ = 25 °C	-	-	-100	nA
	current	$V_{CB} = -80 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	-50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -80 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -8 V; $I_{C}$ = 0 A; $T_{amb}$ = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; $T_{amb}$ = 25 °C	170	305	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C; pulsed	160	275	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -3 A; $t_{p}$ ≤ 300 µs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C; pulsed	45	90	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -6 A; pulsed; $t_{p} \le 300 \text{ μs}; \delta \le 0.02; T_{amb}$ = 25 °C	10	20	-	
V <sub>CEsat</sub> collector-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -50 mA; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-75	-130	mV	
		$I_{C}$ = -3 A; $I_{B}$ = -300 mA; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	-	-150	-240	mV
		$I_C$ = -6 A; $I_B$ = -600 mA; pulsed; $t_p \le 300 \text{ μs}$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-900	-1600	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -6 A; $I_B$ = -600 mA; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_{amb}$ = 25 °C; pulsed	-	85	270	mΩ
$V_{BEsat}$	base-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -50 mA; pulsed; $t_p \le 300 \ \mu s$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-0.8	-0.95	V
		$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p \le 300 \ \mu s$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-0.95	-1.1	V
		$I_C$ = -6 A; $I_B$ = -600 mA; pulsed; $t_p \le 300 \text{ μs}$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-1.1	-1.25	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; $T_{amb}$ = 25 °C	-	-0.7	-0.8	V
t <sub>d</sub>	delay time	$V_{CC} = -12.5 \text{ V}; I_C = -3 \text{ A};$	-	15	-	ns
t <sub>r</sub>	rise time	$I_{Bon} = -150 \text{ mA}; I_{Boff} = 150 \text{ mA};$	-	220	-	ns
t <sub>on</sub>	turn-on time	T <sub>amb</sub> = 25 °C	-	235	-	ns
t <sub>s</sub>	storage time		-	160	-	ns
t <sub>f</sub>	fall time		-	185	-	ns
$t_{off}$	turn-off time		-	345	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -500 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	116	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	52	-	pF



 $V_{CE}$  = -2 V

(1)  $T_{amb}$  = 100 °C

(2)  $T_{amb}$  = 25 °C

 $(3) T_{amb} = -55 °C$ 

Fig. 4. DC current gain as a function of collector current; typical values

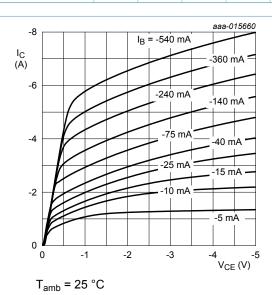
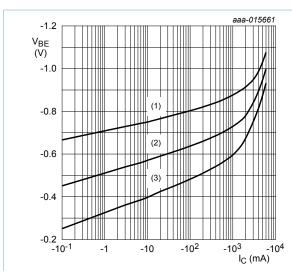


Fig. 5. Collector current as a function of collectoremitter voltage; typical values

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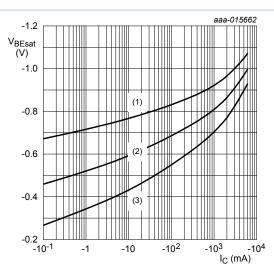
$$V_{CE}$$
 = -2  $V$ 

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb}$$
 = 100 °C

Fig. 6. Base-emitter voltage as a function of collector current; typical values



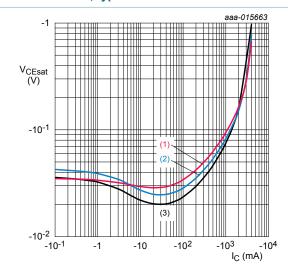
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



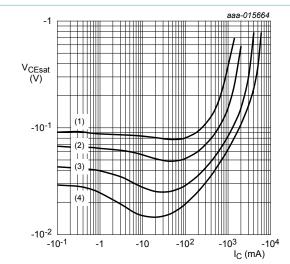
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



(1) 
$$I_C/I_B = 100$$

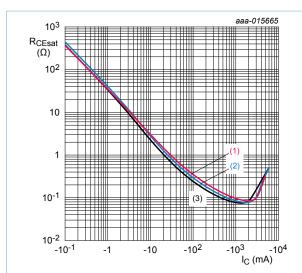
(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 20$$

$$(4) I_C/I_B = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

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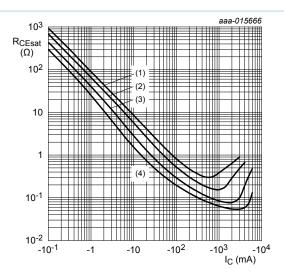
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

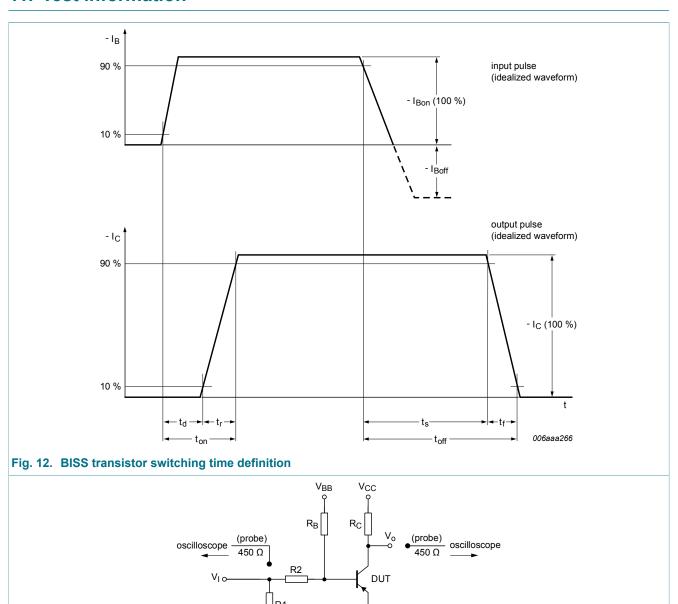
(3) 
$$I_C/I_B = 20$$

(4) 
$$I_C/I_B = 10$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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### 11. Test information



## 11.1 Quality information

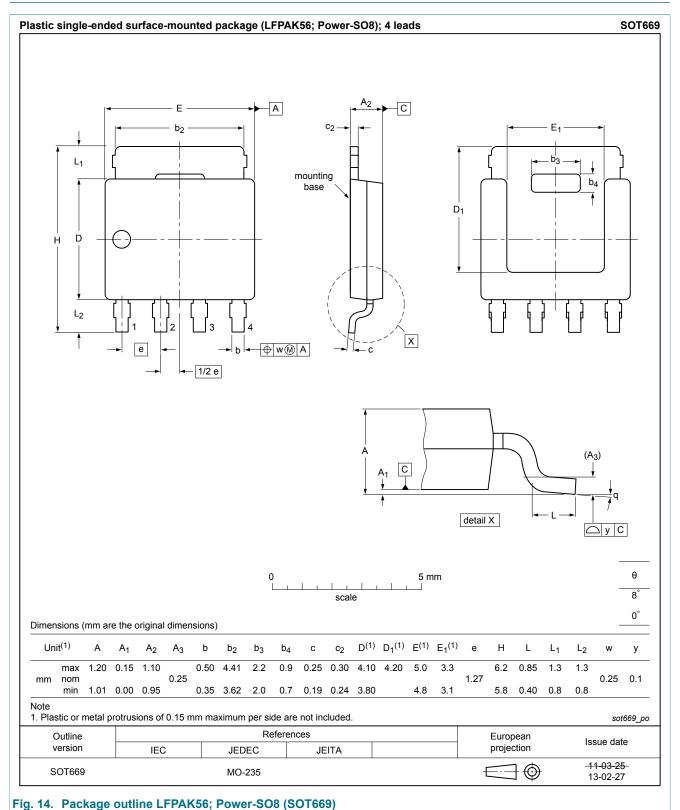
Fig. 13. Test circuit for switching times

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

mgd624

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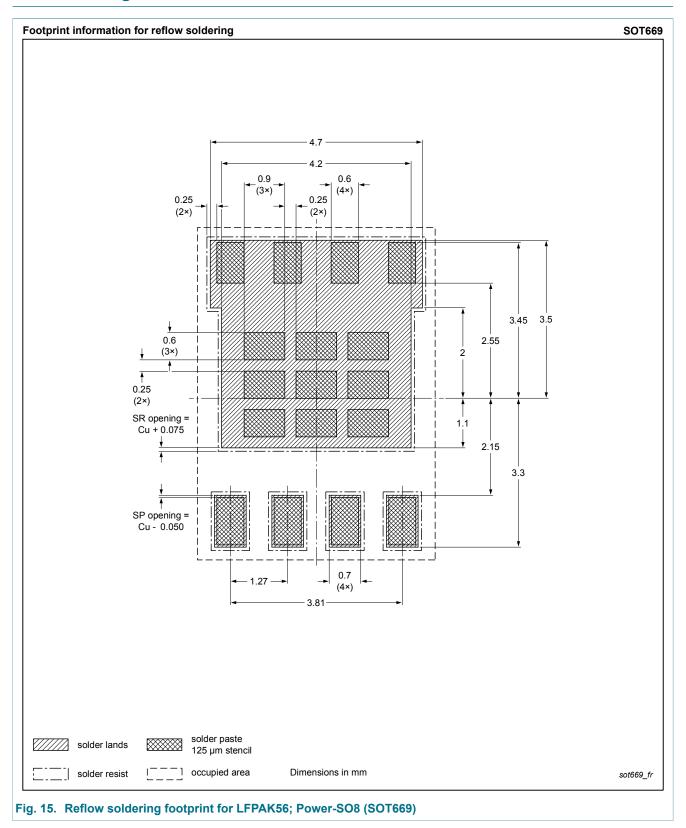
## 12. Package outline



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## 13. Soldering



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## 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61006PY v.1	20150121	Product data sheet	-	-

#### 100 V, 6 A PNP high power bipolar transistor

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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